Ordering number :EN3089B

1SV234

Silicon Epitaxial Type

PIN Diode for VHF, UHF, AGC Applications

Features

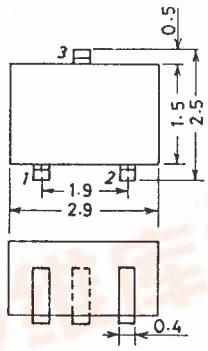
- Series connection of 2 elements in an ultrasmall package facilitates high-density mounting and permits 1SV234-applied equipment to be made smaller.
- Small interterminal capacitance (C=0.23pF typ).
- Small forward series resistance (rs=5Ω typ).

Package Dimensions

unit:mm

1147A

[1SV234]



1:Anode
2:Cathode
3:Cathode,Anode

SANYO:CP

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Reverse Voltage	V_R		50	V
Forward Current	I_F		50	mA
Allowable Power Dissipation	P		150	mW
Junction Temperature	Tj		125	˚C
Storage Temperature	Tstg		–55 to +125	˚C

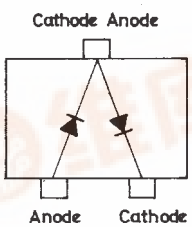
Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=10μA	50			V
Reverse Current	I_R	V_R=50V			0.1	μA
Forward Voltage	V_F	I_F=50mA		0.95		V
Interterminal Capacitance	C	V_R=50V, f=1MHz		0.23		pF
Series Resistance	rs	I_F=10mA, f=100MHz		5		Ω

Note : The specifications shown above are for each individual diode.

· Marking:CV

Electrical Connection



(Top view)

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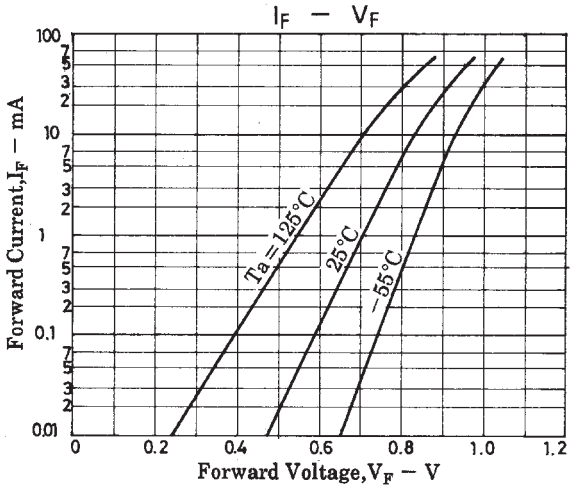
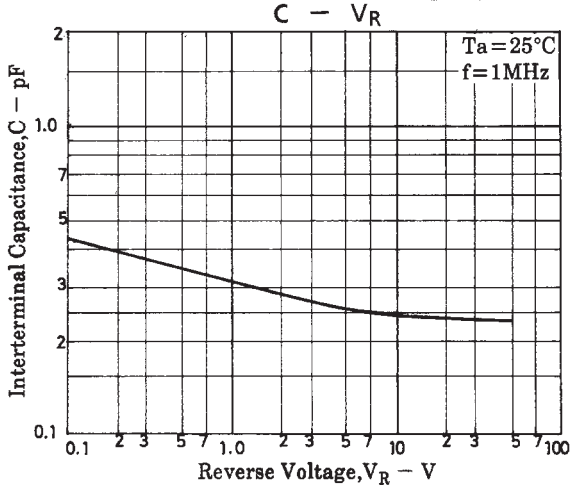
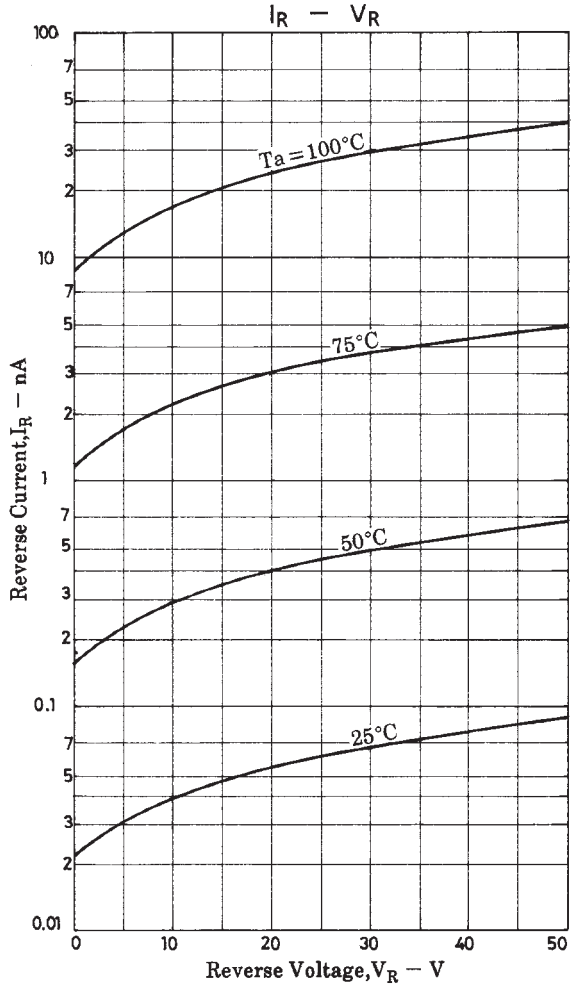
$I_F - V_F$



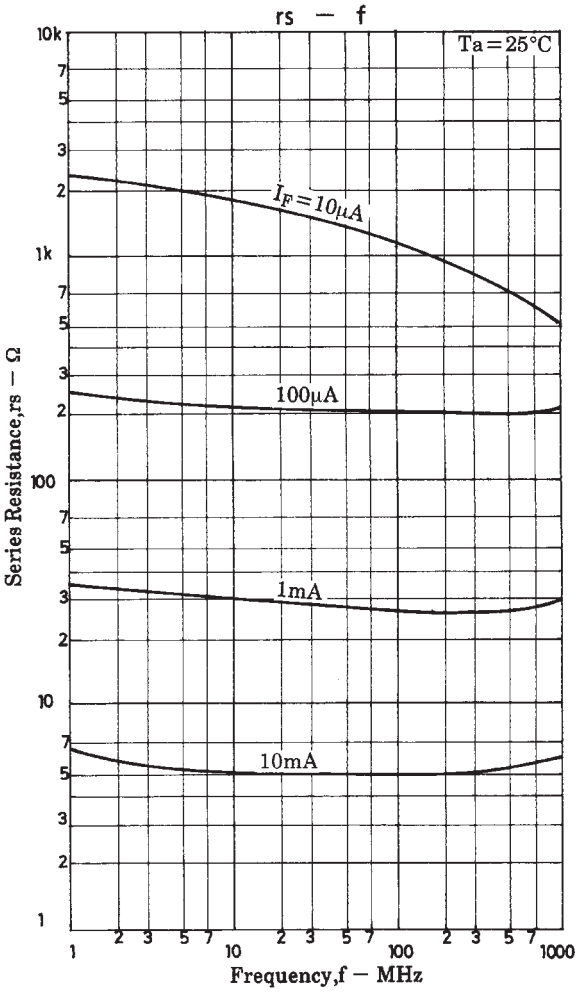
$C - V_R$



$I_R - V_R$



rs – f



rs – I_F